EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	140	(semiconductor or wafer or substrate) and (active near4 region) and "nFET" and "pFET" and (gate near4 electrode)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/21 10:59
L2	1	(semiconductor or wafer or substrate) and (active near4 region) and "nFET" and "pFET" and (gate near4 electrode) and (bond\$4 near4 (semiconductor or wafer or substrate)) and (open\$4 or via or trench or hole) and (implant\$4 near4 oxygen) and (anneal or heat or thermal) and stress and (current near8 flow)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/21 11:05
L3	4	(semiconductor or wafer or substrate) and (active near4 region) and "nFET" and "pFET" and (gate near4 electrode) and (bond\$4 near4 (semiconductor or wafer or substrate)) and (open\$4 or via or trench or hole) and stress and (current near8 flow)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/21 11:56
L4	13	(semiconductor or wafer or substrate) and (active near4 region) and "nFET" and "pFET" and (gate near4 electrode) and (bond\$4 near4 (semiconductor or wafer or substrate)) and (open\$4 or via or trench or hole) and stress	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/21 11:57
L5	9	(semiconductor or wafer or substrate) and (active near4 region) and "nFET" and "pFET" and (gate near4 electrode) and (bond\$4 near4 (semiconductor or wafer or substrate)) and (open\$4 or via or trench or hole) and stress and direction	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/21 13:47
L6	6	(semiconductor or wafer or substrate) and (active near4 region) and "nFET" and "pFET" and (gate near4 electrode) and (bond\$4 near4 (semiconductor or wafer or substrate)) and (implant\$4 near4 oxygen)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/21 13:48

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L7 6	(semiconductor or wafer or substrate) and (active near4 region) and "nFET" and "pFET" and (gate near4 electrode) and (bond\$4 near4 (semiconductor or wafer or substrate)) and (implant\$4 near4 oxygen) and (anneal or thermal or heat)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/21 13:48
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